AMENDMENTS TO THE CLAIMS:

Please amend the claims as follows:

Claims 1-5. (Canceled)

6. (Previously Presented) The method of claim 7, wherein

in the oxide film forming step, the chemical oxide film is grown on the substrate surface by applying voltage to the substrate on which the chemical oxide film is to be formed.

7. (Previously Presented) A method of manufacturing a thin film transistor including an oxide film, the method comprising an oxide film forming step comprising

immersing a substrate in an oxidizing solution containing an active oxidizing species for direct oxidation of the substrate to form a chemical oxide film, the substrate having a surface on which a chemical oxide film is to be formed,

the substrate on which the chemical oxide film is to be formed contains, on the surface, at least one component selected from the group consisting of monocrystal silicon, polycrystalline silicon, amorphous silicon, continuous grain silicon, silicon carbide, and silicon germanium.

Claim 8. (Canceled)

9. (Previously Presented) A method of manufacturing a thin film transistor including an oxide film, the method comprising an oxide film forming step comprising

immersing a substrate in an oxidizing solution containing an active oxidizing species for direct oxidation of the substrate to form a chemical oxide film, the substrate having a surface on which a chemical oxide film is to be formed,

wherein

the oxidizing solution is an azeotropic mixture containing: at least one solution selected from the group consisting of nitric acid, perchloric acid, sulfuric acid, ozone-dissolving water, aqueous hydrogen peroxide, a mixed solution of hydrochloric acid and aqueous hydrogen peroxide, a mixed solution of sulfuric acid and aqueous hydrogen peroxide, a mixed solution of aqueous ammonia and aqueous hydrogen peroxide, a mixed solution of sulfuric acid and nitric acid, aqua regia, and boiling water; a gas thereof; or a mixed solution thereof.

10. (Original) The method of claim 9, wherein

the oxidizing solution contains at least one solution selected from the group consisting of azeotropic nitric acid which is an azeotropic mixture with water, azeotropic sulfuric acid which is an azeotropic mixture with water, and azeotropic perchloric acid which is an azeotropic mixture with water.

11. (Currently Amended) The method of claim [[4]]13, wherein

the oxide film forming step is carried out at 200°C or lower temperatures.

12. (Currently Amended) The method of claim [[4]]13, further comprising, after forming the chemical oxide film, a step of forming an insulating film on the chemical oxide film.

13. (Previously Presented) A method of manufacturing a thin film transistor including an oxide film, the method comprising an oxide film forming step comprising

immersing a substrate in an oxidizing solution containing an active oxidizing species below azeotropic concentration for direct oxidation of the substrate to form a

first chemical oxide film, the substrate having a surface on which a chemical oxide film is to be formed; and

concentrating the oxidizing solution below azeotropic concentration up to or in excess of an azeotropic concentration with the substrate being immersed in that oxidizing solution to form a second oxide film on the first oxide film.

14. (Original) The method of claim 7, wherein

the substrate on which the chemical oxide film is to be formed contains silicon carbide on the surface.

15. (Previously Presented) The method of claim 9, wherein

the oxidizing solution is nitric acid.

16. (Currently Amended) The method of claim [[4]]13, further comprising, after the oxide film forming step, the step of subjecting the chemical oxide film[[(s)]] to nitriding.

17. (Previously Presented) A thin film transistor manufactured by the method of claim 7, comprising the chemical oxide film formed by oxidation in an oxidizing solution.

18. (Original) A thin film transistor of claim 17, wherein the chemical oxide film has a relatively high atomic density near the substrate.

Claim 19. (Canceled)

20. (Previously Presented) A display containing the thin film transistor of claim 17.

21. (Previously Presented) A method of modifying an oxide film, comprising the step of

performing the oxide film forming step of claim 7 on an oxide film having a non-uniform thickness to improve quality of the oxide film.

22. (Previously Presented) A method of modifying an oxide film, comprising the step of

performing the oxide film forming step of claim 7 on an oxide film having non-uniform quality to improve the quality of the oxide film.

Claims 23-34. (Canceled)